T-25-13

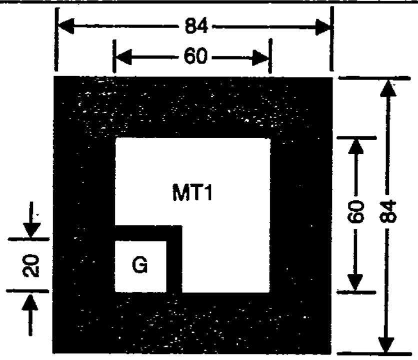
SILICON THYRISTOR DIE (continued)

CHIP NO. 2C6075
LINE SOURCE — DTL0401

TRIAC — Bidirectional
Triode Thyristor

Device assembled from this die type are similar to or better than the following device types:

2N6068	**2N6072**
2N6069	**2N6073**
2N6070	**2N6074**
2N6071	**2N6075**



Metallized portion of backside is MT2

METALLIZATION —

Top	Al
Back	Al, Cr, Cu, Au

CHIP THICKNESS	8.5 ± 0.5 mils

BONDING PAD SIZE:

Anode	60 mils
Cathode	60 mils
Gate	20 mils
Glassivation	yes

ELECTRICAL CHARACTERISTICS (T_A = 25°C, See Note 1)

Parameter	Test Conditions	Min	Max	Unit
I_{DRM}	V_D = 400 Vdc	—	20	μAdc
I_{GT}	V_D = 12 Vdc, R_L = 100 Ω			mAdc
	MT2(+), G(+)	—	30	
	MT2(+), G(−)	—	30	
	MT2(−), G(−)	—	30	
	MT2(−), G(+)	—	40	
V_{GT}	V_D = 12 Vdc, R_L = 100 Ω			Volts
	MT2(+), G(+)	—	2.0	
	MT2(+), G(−)	—	2.0	
	MT2(−), G(−)	—	2.0	
	MT2(−), G(+)	—	2.5	
I_H	V_D = 12 Vdc, I_{TH} = 0.2 Adc	—	30	mAdc

NOTES: 1. Because of the limitation of probe testing, dc parameters are tested. These parameters must be measured using pulse techniques pulse width = 300 μA duty cycle ≤ 2%.

Chip characteristics, including curves, are available from current Discrete Motorola Data.